

**1. Material**            Substrate      GaAs (N Type)  
                                  Epitaxial Layer GaAs (P/N Type)

**2. Electrode**            N(Cathode) Side Gold Alloy  
                                  P(Anode) Side Gold Alloy

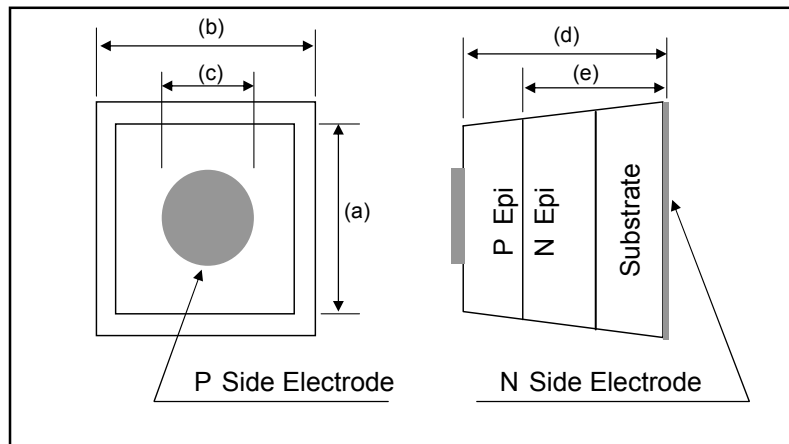
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.65	1.75	V	IF=100mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	11	21		mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

(a) Emission Area	-----	7mil x	7mil
(b) Bottom Area	-----	8mil x	8mil
(c) Bonding Pad	-----	110um	
(d) Chip Thickness	-----	9.0mil	
(e) Junction Height	-----	6.5mil	



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